

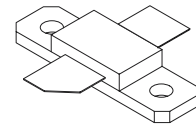
The RF Sub-Micron MOSFET Line
RF Power Field Effect Transistors
N-Channel Enhancement-Mode Lateral MOSFETs

Designed for broadband commercial and industrial applications with frequencies up to 1.0 GHz. The high gain and broadband performance of these devices make them ideal for large-signal, common-source amplifier applications in 26 volt base station equipment.

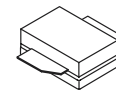
- Typical Two-Tone Performance at 945 MHz, 26 Volts
Output Power — 30 Watts PEP
Power Gain — 19 dB
Efficiency — 41.5%
IMD — -32.5 dBc
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Capable of Handling 10:1 VSWR, @ 26 Vdc, 945 MHz, 30 Watts CW Output Power
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- In Tape and Reel. R1 Suffix = 500 Units per 32 mm, 13 inch Reel.

MRF9030R1
MRF9030SR1

945 MHz, 30 W, 26 V
LATERAL N-CHANNEL
BROADBAND
RF POWER MOSFETs



CASE 360B-05, STYLE 1
NI-360
MRF9030R1



CASE 360C-05, STYLE 1
NI-360S
MRF9030SR1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	68	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +15	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	92 0.53	Watts $\text{W}/^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	117 0.67	Watts $\text{W}/^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +200	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

ESD PROTECTION CHARACTERISTICS

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M1 (Minimum)

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.9 1.5	$^\circ\text{C}/\text{W}$

NOTE – **CAUTION** – MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

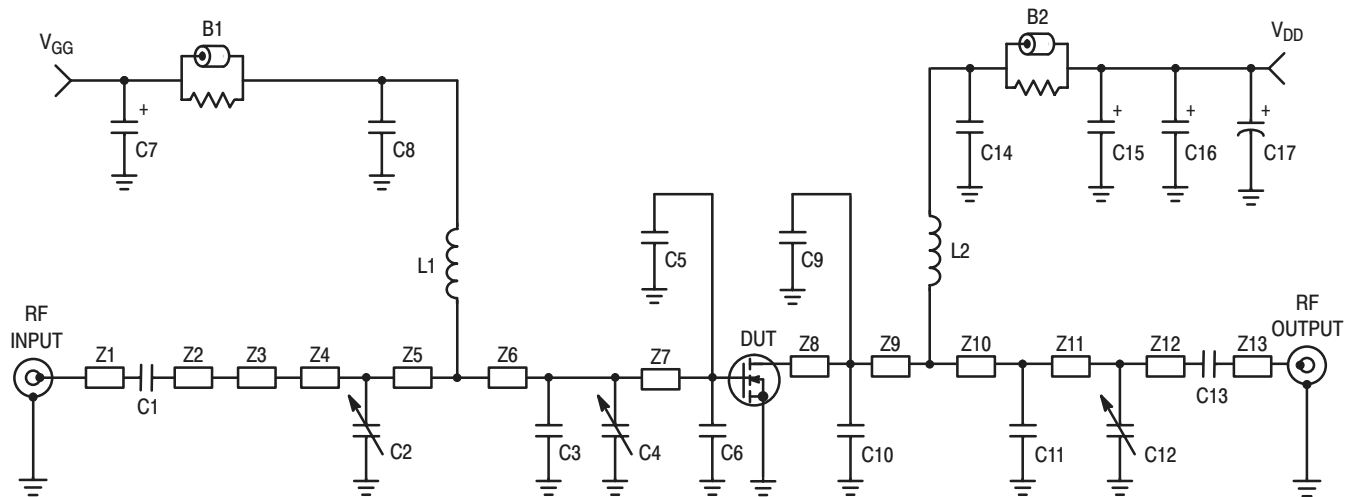
ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 68\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate–Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc
ON CHARACTERISTICS					
Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 100\ \mu\text{Adc}$)	$V_{GS(th)}$	2	2.9	4	Vdc
Gate Quiescent Voltage ($V_{DS} = 26\text{ Vdc}$, $I_D = 250\text{ mAdc}$)	$V_{GS(Q)}$	—	3.8	—	Vdc
Drain–Source On–Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 0.7\text{ Adc}$)	$V_{DS(on)}$	—	0.19	0.4	Vdc
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 2\text{ Adc}$)	g_{fs}	—	3	—	S
DYNAMIC CHARACTERISTICS					
Input Capacitance ($V_{DS} = 26\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{iss}	—	49.5	—	pF
Output Capacitance ($V_{DS} = 26\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{oss}	—	26.5	—	pF
Reverse Transfer Capacitance ($V_{DS} = 26\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	1	—	pF

(continued)

ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
FUNCTIONAL TESTS (In Motorola Test Fixture, 50 ohm system)					
Two-Tone Common-Source Amplifier Power Gain ($V_{DD} = 26$ Vdc, $P_{out} = 30$ W PEP, $I_{DQ} = 250$ mA, $f_1 = 945.0$ MHz, $f_2 = 945.1$ MHz)	G_{ps}	18	19	—	dB
Two-Tone Drain Efficiency ($V_{DD} = 26$ Vdc, $P_{out} = 30$ W PEP, $I_{DQ} = 250$ mA, $f_1 = 945.0$ MHz, $f_2 = 945.1$ MHz)	η	37	41.5	—	%
3rd Order Intermodulation Distortion ($V_{DD} = 26$ Vdc, $P_{out} = 30$ W PEP, $I_{DQ} = 250$ mA, $f_1 = 945.0$ MHz, $f_2 = 945.1$ MHz)	IMD	—	-32.5	-28	dBc
Input Return Loss ($V_{DD} = 26$ Vdc, $P_{out} = 30$ W PEP, $I_{DQ} = 250$ mA, $f_1 = 945.0$ MHz, $f_2 = 945.1$ MHz)	IRL	—	-15.5	-9	dB
Two-Tone Common-Source Amplifier Power Gain ($V_{DD} = 26$ Vdc, $P_{out} = 30$ W PEP, $I_{DQ} = 250$ mA, $f_1 = 930.0$ MHz, $f_2 = 930.1$ MHz and $f_1 = 960.0$ MHz, $f_2 = 960.1$ MHz)	G_{ps}	—	19	—	dB
Two-Tone Drain Efficiency ($V_{DD} = 26$ Vdc, $P_{out} = 30$ W PEP, $I_{DQ} = 250$ mA, $f_1 = 930.0$ MHz, $f_2 = 930.1$ MHz and $f_1 = 960.0$ MHz, $f_2 = 960.1$ MHz)	η	—	41.5	—	%
3rd Order Intermodulation Distortion ($V_{DD} = 26$ Vdc, $P_{out} = 30$ W PEP, $I_{DQ} = 250$ mA, $f_1 = 930.0$ MHz, $f_2 = 930.1$ MHz and $f_1 = 960.0$ MHz, $f_2 = 960.1$ MHz)	IMD	—	-33	—	dBc
Input Return Loss ($V_{DD} = 26$ Vdc, $P_{out} = 30$ W PEP, $I_{DQ} = 250$ mA, $f_1 = 930.0$ MHz, $f_2 = 930.1$ MHz and $f_1 = 960.0$ MHz, $f_2 = 960.1$ MHz)	IRL	—	-14	—	dB
Power Output, 1 dB Compression Point ($V_{DD} = 26$ Vdc, $P_{out} = 30$ W CW, $I_{DQ} = 250$ mA, $f_1 = 945.0$ MHz)	P_{1dB}	—	30	—	W
Common-Source Amplifier Power Gain ($V_{DD} = 26$ Vdc, $P_{out} = 30$ W CW, $I_{DQ} = 250$ mA, $f_1 = 945.0$ MHz)	G_{ps}	—	19	—	dB
Drain Efficiency ($V_{DD} = 26$ Vdc, $P_{out} = 30$ W CW, $I_{DQ} = 250$ mA, $f_1 = 945.0$ MHz)	η	—	60	—	%
Output Mismatch Stress ($V_{DD} = 26$ Vdc, $P_{out} = 30$ W CW, $I_{DQ} = 250$ mA, $f = 945.0$ MHz, VSWR = 10:1, All Phase Angles at Frequency of Tests)	Ψ	No Degradation In Output Power			



B1	Short Ferrite Bead	Z3	0.500" x 0.100" Microstrip
B2	Long Ferrite Bead	Z4	0.215" x 0.270" Microstrip
C1, C8, C13, C14	47 pF Chip Capacitors, B Case	Z5	0.315" x 0.270" Microstrip
C2, C4	0.8 pF to 8.0 pF Trim Capacitors	Z6	0.160" x 0.270" x 0.520", Taper
C3	3.9 pF Chip Capacitor, B Case	Z7	0.285" x 0.520" Microstrip
C5, C6	7.5 pF Chip Capacitors, B Case	Z8	0.140" x 0.270" Microstrip
C7, C15, C16	10 μ F, 35 V Tantalum Capacitors	Z9	0.450" x 0.270" Microstrip
C9, C10	10 pF Chip Capacitors, B Case	Z10	0.250" x 0.060" Microstrip
C11	9.1 pF Chip Capacitor, B Case	Z11	0.720" x 0.060" Microstrip
C12	0.6 pF to 4.5 pF Trim Capacitor	Z12	0.490" x 0.060" Microstrip
C17	220 μ F, 50 V Electrolytic Capacitor	Z13	0.290" x 0.060" Microstrip
L1, L2	12.5 nH Surface Mount Inductors	Board	Taconic RF-35-0300, ($\epsilon_r = 3.5$) CAX1/CAX1
Z1	0.260" x 0.060" Microstrip		
Z2	0.240" x 0.060" Microstrip		

Figure 1. 945 MHz Broadband Test Circuit Schematic

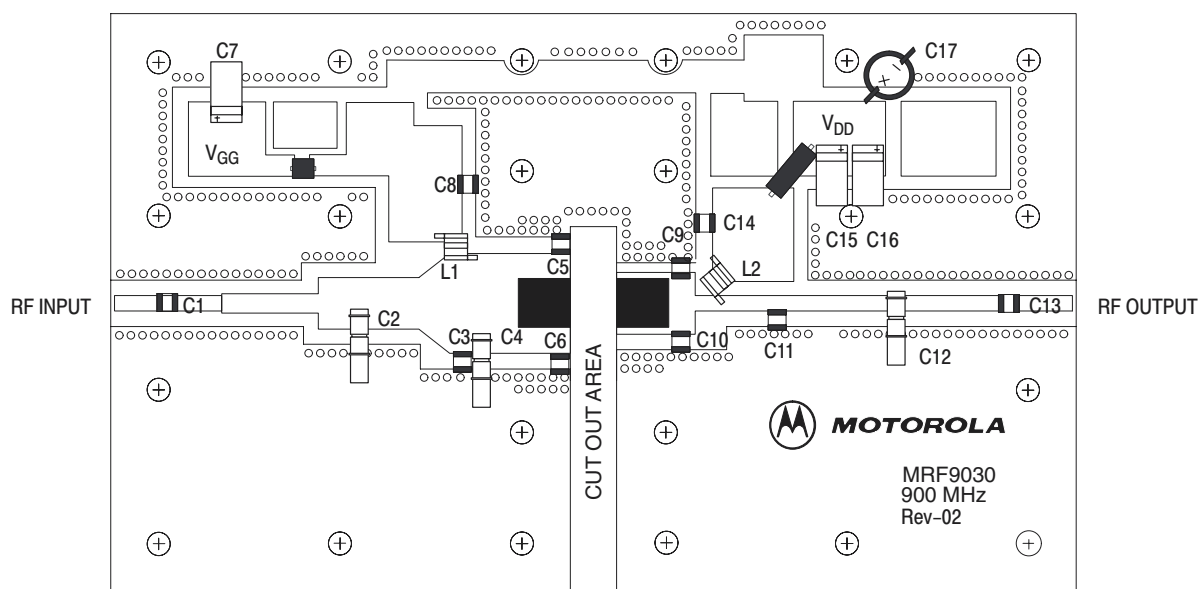


Figure 2. 945 MHz Broadband Test Circuit Component Layout

TYPICAL CHARACTERISTICS

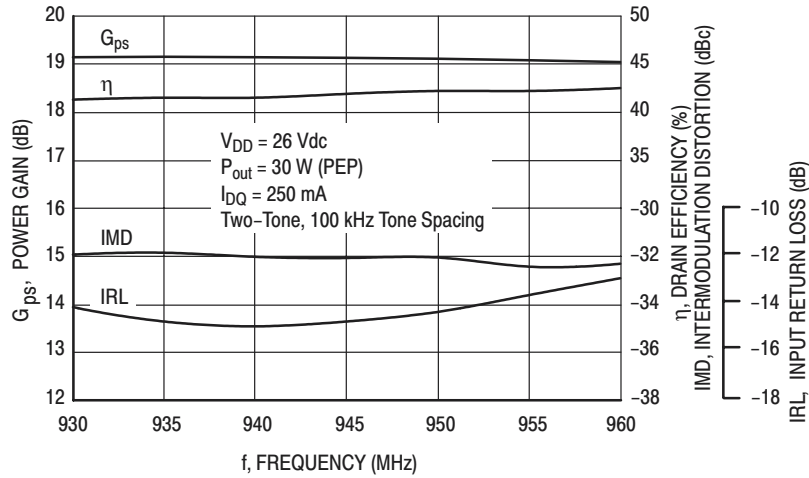


Figure 3. Class AB Broadband Circuit Performance

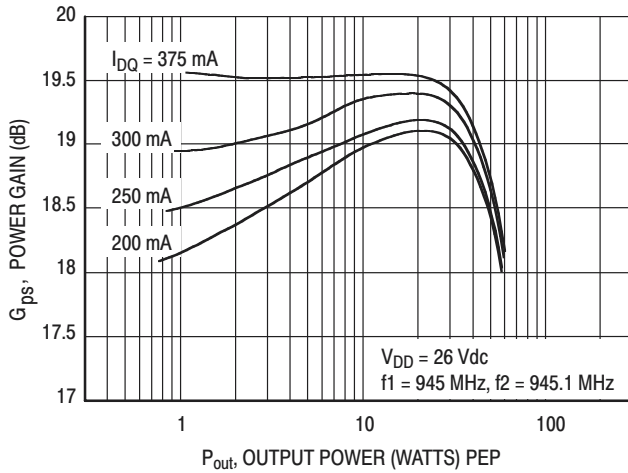


Figure 4. Power Gain versus Output Power

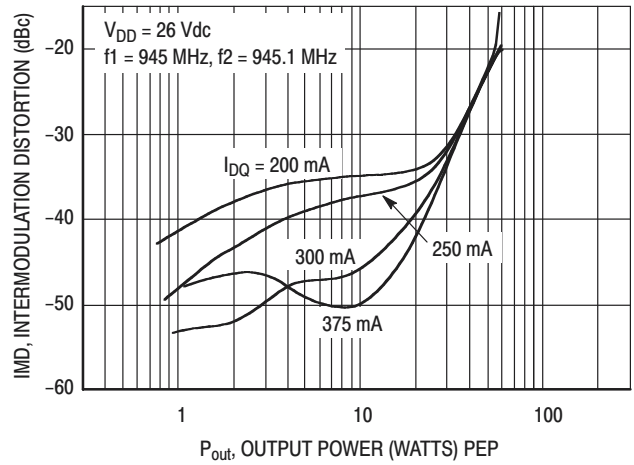


Figure 5. Intermodulation Distortion versus Output Power

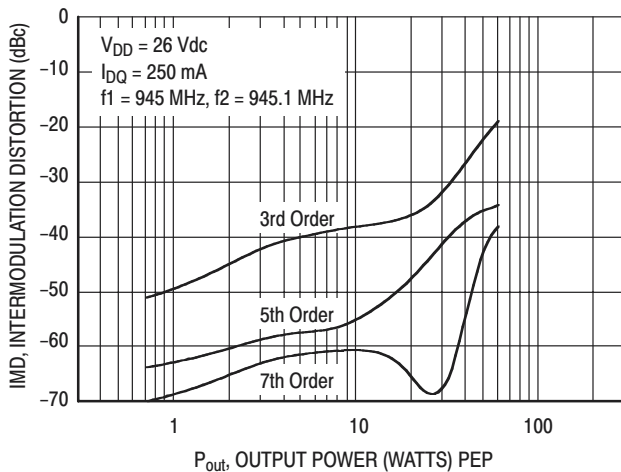


Figure 6. Intermodulation Distortion Products versus Output Power

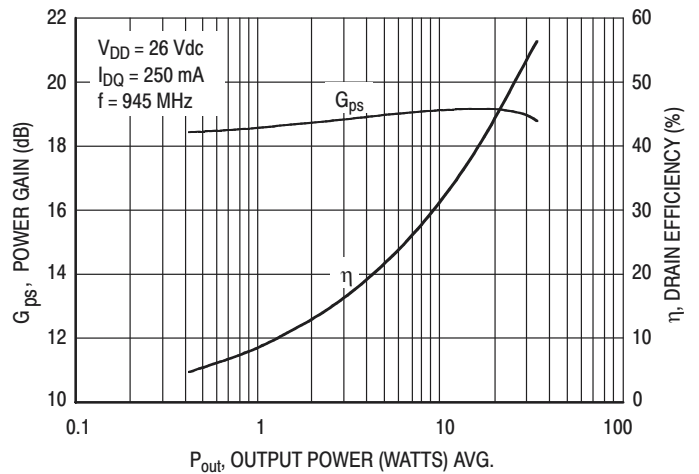


Figure 7. Power Gain and Efficiency versus Output Power

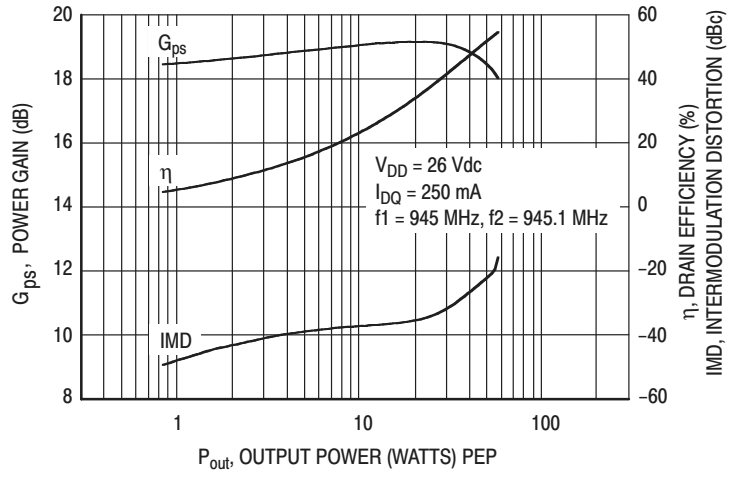
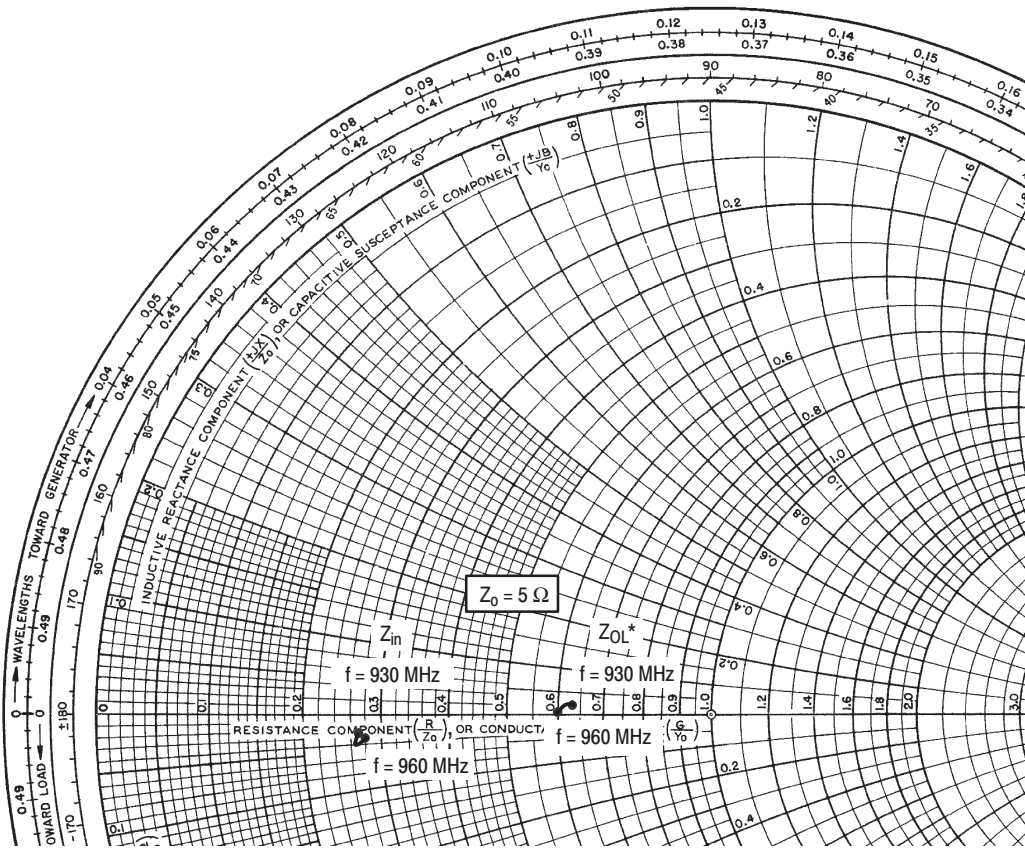


Figure 8. Power Gain, Efficiency and IMD versus Output Power



$V_{DD} = 26 \text{ V}$, $I_{DQ} = 250 \text{ mA}$, $P_{out} = 30 \text{ W PEP}$

f MHz	Z_{in} Ω	Z_{OL}^* Ω
930	$1.34 - j0.1$	$3.175 + j0.09$
945	$1.36 - j0.2$	$3.1 + j0.08$
960	$1.4 - j0.14$	$3.0 + j0.05$

Z_{in} = Complex conjugate of source impedance.

Z_{OL}^* = Complex conjugate of the optimum load impedance at a given output power, voltage, IMD, bias current and frequency.

Note: Z_{OL}^* was chosen based on tradeoffs between gain, output power, drain efficiency and intermodulation distortion.

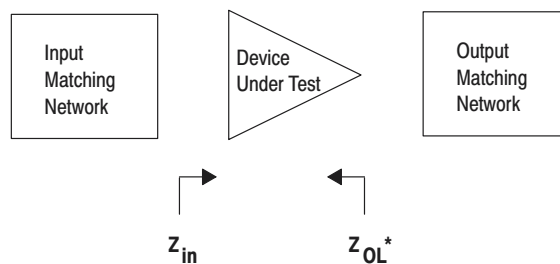


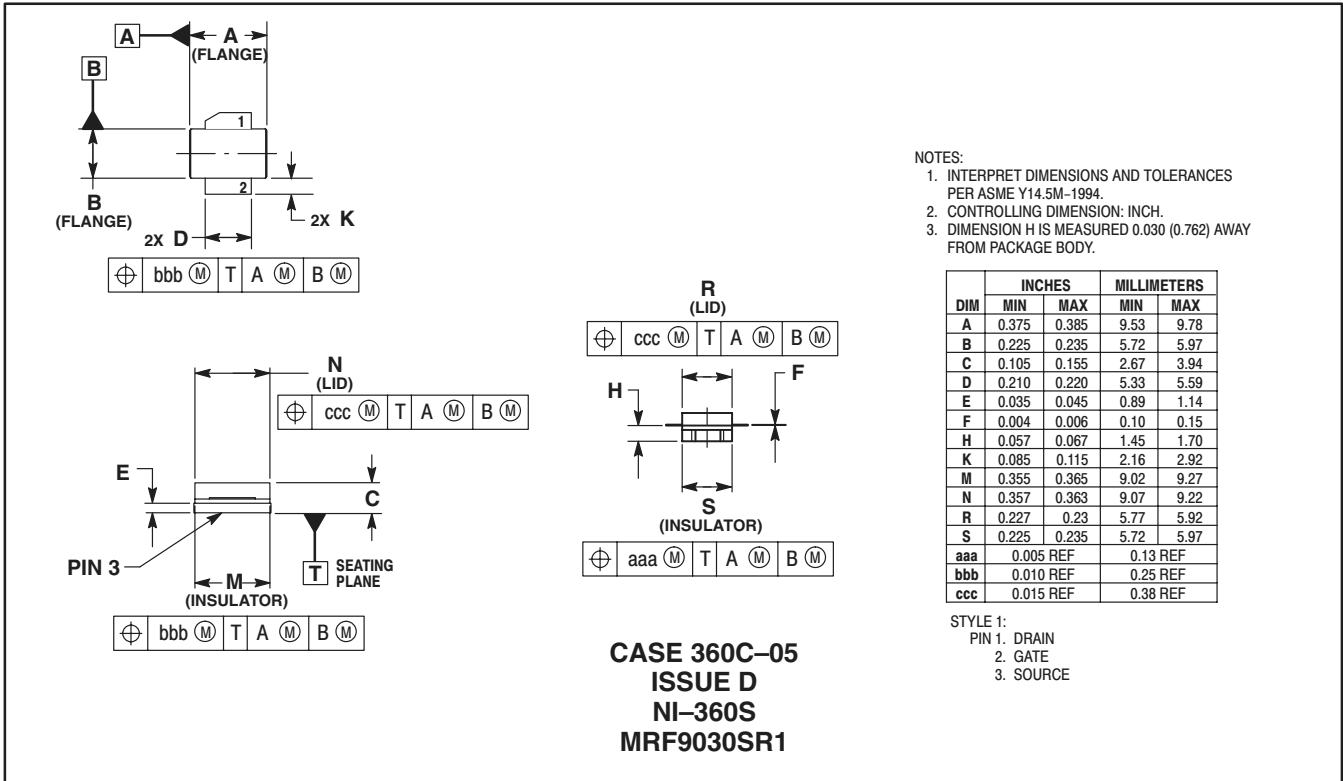
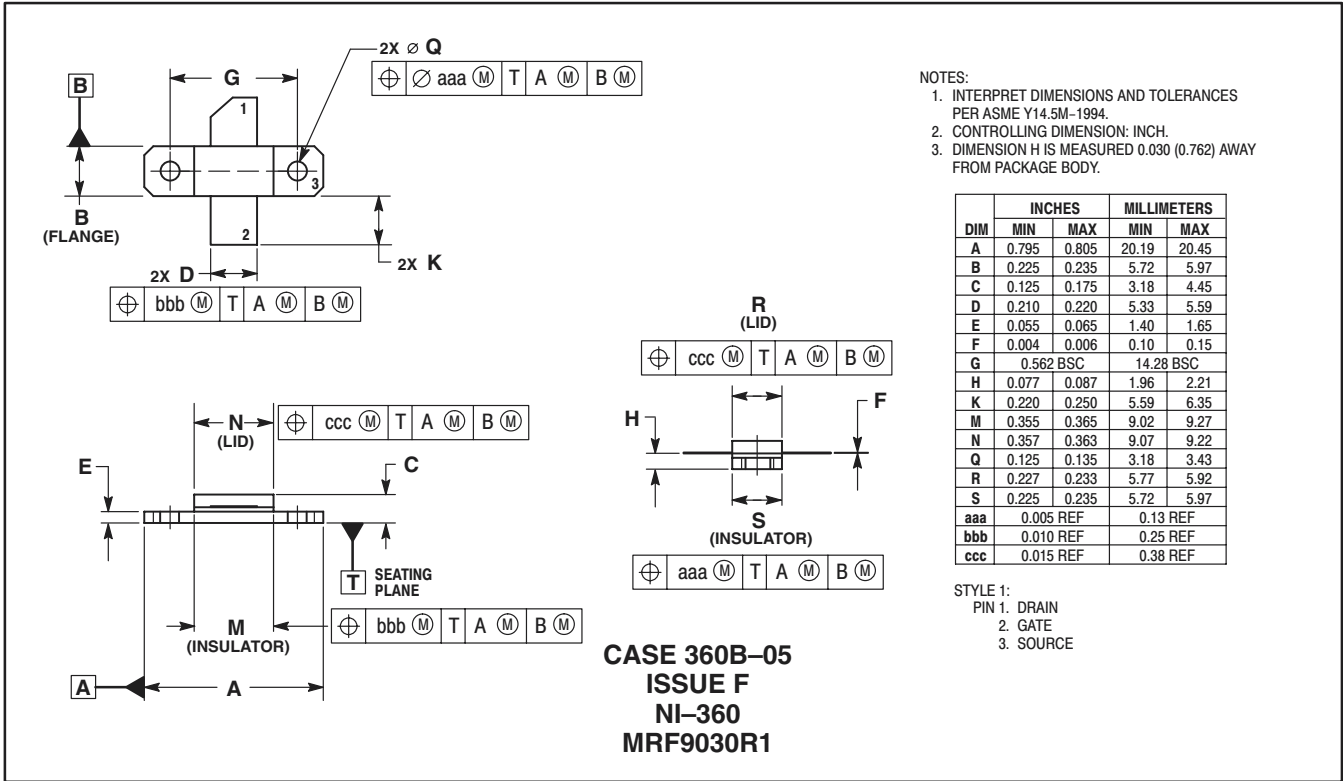
Figure 9. Series Equivalent Input and Output Impedance


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PACKAGE DIMENSIONS



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